

L Number	Hits	Search Text	DB	Time stamp
1	2710	(385/88-94).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:40
2	466	semiconductor with wafer with cap	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:40
3	1	((385/88-94).CCLS.) and (semiconductor with wafer with cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:40
4	0	20020090180.URPN.	USPAT	2003/06/28 14:40
5	3114	(385/88-94,139).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:43
6	1	((385/88-94,139).CCLS.) and (semiconductor with wafer with cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:40
7	976	(semiconductor with wafer) and (wafer with cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:41
8	3	((385/88-94,139).CCLS.) and ((semiconductor with wafer) and (wafer with cap))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:41
9	1	hammond.in. and song.xa.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:43
10	4027	wafer adj level	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:43
11	63	((semiconductor with wafer) and (wafer with cap)) and (wafer adj level)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:48
12	9	((semiconductor with wafer) and (wafer with cap)) and (wafer adj level)) and (resist near cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:49
14	0	((((semiconductor with wafer and (wafer with cap)) and (wafer adj level)) and (photoresist near cap)) not (((semiconductor with wafer and (wafer with cap)) and (wafer adj level)) and (resist near cap)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:49
13	9	((semiconductor with wafer) and (wafer with cap)) and (wafer adj level)) and (photoresist near cap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/28 14:50

15	0	(semiconductor with wafer with cap) and (photoresist near cap)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 14:51
16	0	((385/88-94).CCLS.) and (photoresist near cap)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 14:51
17	14	wafer same (photoresist near cap)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 14:52
18	17	cap near (back bottom) with wafer	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 14:58
20	2	(deep adj silicon adj etch) and 385/88.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 14:59
19	100	deep adj silicon adj etch	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 15:00
21	2	(semiconductor with wafer with cap) and (deep adj silicon adj etch)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 15:00
22	17	((semiconductor with wafer) and (wafer with cap)) and (deep adj silicon adj etch)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 15:11
23	11	("4742432" "4899587" "5230759" "5556776" "5799557" "5824177" "5915168" "9923995" "6136212" "6255741" "6379398").PN.	USPAT	2003/06/28 15:07
24	3551	wafer same ((etch etching etched) with (separat\$3 divid\$3))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 15:12
25	2311	wafer with((etch etching etched) with (separat\$3 divid\$3))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 15:14
26	102	wafer with((etch etching etched) with (separat\$3 divid\$3) with chip\$1 with (sawing dicing sawed diced cut cutting))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 15:15
27	14	("3963489" "4047184" "4071944" "4679299" "4710263" "4818712" "4822755" "5075256" "5429954" "5597766" "5622900" "5637189" "5770884" "5789307").PN.	USPAT	2003/06/28 15:25
28	39	((385/88-94,139).CCLS.) and (wafer adj level)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM TDB	2003/06/28 15:43